Complementary Power Transistors

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain-Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CB}	70	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current	I _C	10	Adc
Base Current	Ι _Β	6	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D [†]	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

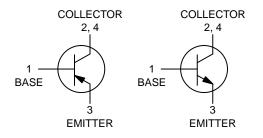


ON Semiconductor®

http://onsemi.com

SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

COMPLEMENTARY





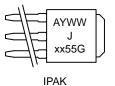


DPAK CASE 369C STYLE 1

IPAK CASE 369D STYLE 1

MARKING DIAGRAMS





DPAK

A = Assembly Location

Y = Year WW = Work Week Jxx55 = Device Code x = 29 or 30

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

[†]Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	*		1	4
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	60	_	Vdc
Collector Cutoff Current $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$	I _{CEO}	_	50	μAdc
Collector Cutoff Current $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	I _{CEX}	- -	0.02 2	mAdc
Collector Cutoff Current $(V_{CB} = 70 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 70 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C})$	Ісво	- -	0.02 2	mAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) (I _C = 4 Adc, V _{CE} = 4 Vdc) (I _C = 10 Adc, V _{CE} = 4 Vdc)	h _{FE}	20 5	100	-
Collector–Emitter Saturation Voltage (Note 3) (I _C = 4 Adc, I _B = 0.4 Adc) (I _C = 10 Adc, I _B = 3.3 Adc)	V _{CE(sat)}	- -	1.1 8	Vdc
Base–Emitter On Voltage (Note 3) (I _C = 4 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	-	1.8	Vdc
DYNAMIC CHARACTERISTICS	·			
Current–Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f = 500 kHz)	f _T	2	_	MHz
Pulse Test: Pulse Width < 300 us Duty Cycle < 2%	+			

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

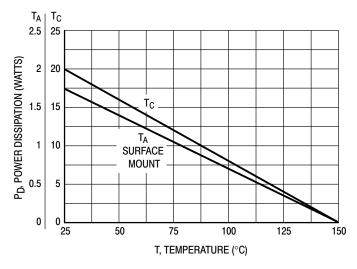


Figure 1. Power Derating

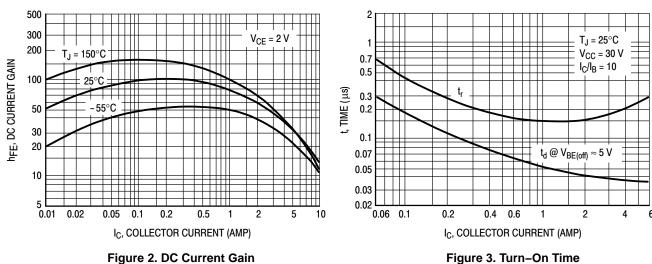


Figure 2. DC Current Gain

V, VOLTAGE (VOLTS)

1.4 $T_J = 25^{\circ}C$ 3 V_{CC} = 30 V 1.2 $T_J = 25^{\circ}C$ 2 $I_C/I_B = 10$ $I_{B1} = I_{B2}$ t, TIME (µs) 8.0 $V_{BE(sat)} @ I_C/I_B = 10$ 0.7 0.5 0.6 V_{BE} @ V_{CE} = 2 V 0.3 0.2 $t_{\rm f}$ 0.4 0.1 0.2 $V_{CE(sat)} @ I_C/I_B = 10$ 0.07 0 l 10 0.06 0.1 0.6 0.1 0.2 0.3 I_C, COLLECTOR CURRENT (AMP) I_C, COLLECTOR CURRENT (AMP)

Figure 4. "On" Voltages, MJD3055

Figure 5. Turn-Off Time

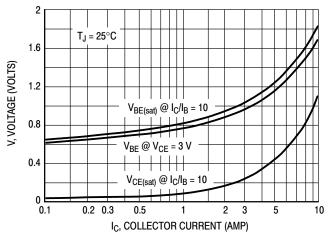
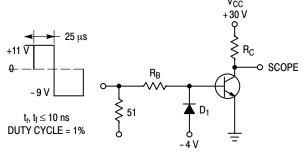


Figure 6. "On" Voltages, MJD2955



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS $D_1 \ \text{MUST BE FAST RECOVERY TYPE, eg:} \\ 1N5825 \ \text{USED ABOVE I}_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW I}_B \approx 100 \ \text{mA}$

Figure 7. Switching Time Test Circuit

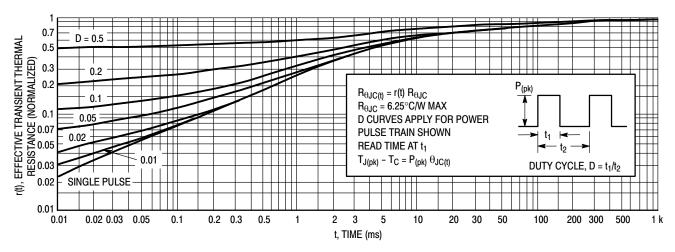


Figure 8. Thermal Response

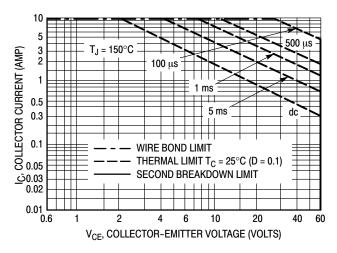


Figure 9. Maximum Forward Bias Safe Operating Area

Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 150^{\circ} C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable



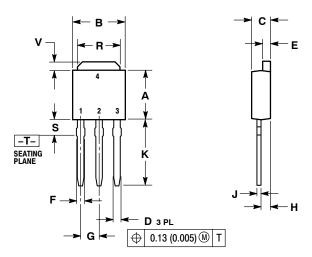


DPAK INSERTION MOUNT

CASE 369 ISSUE O

DATE 02 JAN 2000





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090	BSC	2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
٧	0.030	0.050	0.77	1.27

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		STYLE 5:		STYLE 6:	
PIN 1.	BASE	PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	GATE	PIN 1.	MT1
2.	COLLECTOR	2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE	2.	MT2
3.	EMITTER	3.	SOURCE	3.	ANODE	3.	GATE	3.	CATHODE	3.	GATE
4.	COLLECTOR	4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE	4.	MT2

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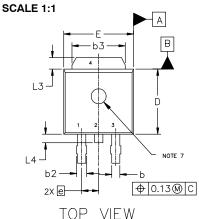
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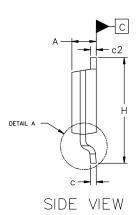




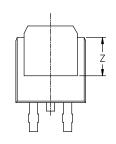
DPAK3 6.10x6.54x2.28, 2.29P CASE 369C **ISSUE J**

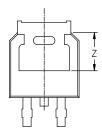
DATE 12 AUG 2025

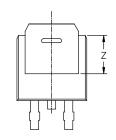


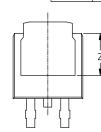


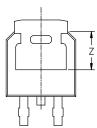
MILLIMETERS					
DIM	MIN	NOM	MAX		
А	2.18	2.28	2.38		
A1	0.00		0.13		
ь	0.63	0.76	0.89		
b2	0.72	0.93	1.14		
b3	4.57	5.02	5.46		
С	0.46	0.54	0.61		
c2	0.46	0.54	0.61		
D	5.97	6.10	6.22		
E	6.35	6.54	6.73		
е	:	2.29 BSC			
Н	9.40	9.91	10.41		
L	1.40	1.59	1.78		
L1	2.90 REF				
L2	0.51 BSC				
L3	0.89		1.27		
L4			1.01		
Z	3.93				











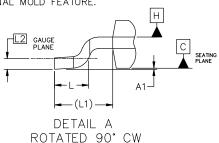
BOTTOM VIEW

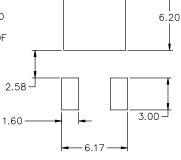
ALTERNATE CONSTRUCTIONS

NOTES:

- DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.

- CONTROLLING DIMENSION: MILLIMETERS.
 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR
 BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15mm PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H. OPTIONAL MOLD FEATURE.





-5.80

RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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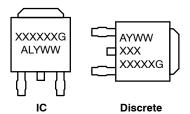
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DPAK3 6.10x6.54x2.28, 2.29P

CASE 369C ISSUE J

DATE 12 AUG 2025

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:	
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE	
COLLECTO	DR 2. DRAIN	CATHODE	2. ANODE	2. ANODE	
EMITTER	3. SOURCE	ANODE	3. GATE	CATHODE	
COLLECTO	DR 4. DRAIN	CATHODE	4. ANODE	4. ANODE	
STVLF 6: ST	VI F 7·	VIF Q: ST	VIF a.	STVLF 10.	

 STYLE 6:
 STYLE 7:
 STYLE 8:
 STYLE 9:
 STYLE 10:

 PIN 1. MT1
 PIN 1. GATE
 PIN 1. N/C
 PIN 1. ANODE
 PIN 1. CATHODE

 2. MT2
 2. COLLECTOR
 2. CATHODE
 2. CATHODE
 2. CATHODE
 2. ANODE

 3. GATE
 3. EMITTER
 3. ANODE
 3. RESISTOR ADJUST
 3. CATHODE
 4. CATHODE
 4. CATHODE
 4. ANODE

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